

This listing of claims will replace all prior versions, and listings, of claims in the application:

**The Status of the Claims**

1. (Original) A method for fabricating a capacitor of a semiconductor device comprising:  
  
forming a first insulating layer by nitrifying a semiconductor substrate using a forming gas;  
  
forming a second insulating layer by depositing a transition element on the first insulating layer and performing a reoxidation process;  
  
forming a third insulating layer by nitrifying the second insulating layer using a forming gas; and  
  
forming a conducting layer on top of the third insulating layer.
2. (Original) A method as defined in claim 1, wherein a conducting layer is formed on the semiconductor substrate prior to forming the first insulating layer.
3. (Original) A method as defined in claim 1, wherein the forming gas comprises N<sub>2</sub> gas or a gas mixture including N<sub>2</sub>.
4. (Original) A method as defined in claim 1, wherein at least one of the first insulating layer, the second insulating layer, and the third

insulating layer is formed using a furnace process.

5. (Original) A method as defined in claim 4, wherein the furnace process is performed at a temperature of about 200~450°C.

6. (Original) A method as defined in claim 1, wherein the transition element is one of Ta, Al, Zr, V, Ti, Ni and Hf.

7. (Original) A method as defined in claim 1, wherein the transition element is deposited by PVD or CVD.

8. (Original) A method as defined in claim 1, wherein the reoxidation process is performed at a temperature of about 700~950°C by a rapid thermal treatment method.

9. (Original) A method as defined in claim 1, wherein the second insulating layer has a thickness of about 5~500 Å.

10. (Original) A method as defined in claim 1, wherein the conducting layer comprises one of: polysilicon, Si, Al, V, Ni, Cu, Co, W, Ta, Ti, and an alloy comprising at least one of polysilicon, Si, Al, V, Ni, Cu, Co, W, Ta, and Ti.

11. (Original) A method as defined in claim 1, wherein the conducting layer is formed by PVD or CVD.

12. (Original) A method as defined in claim 1, wherein the substrate includes at least a predetermined capacitor structure.

13. (Original) A method for fabricating a capacitor of a semiconductor device comprising:

- forming a first insulating layer by nitrifying a semiconductor substrate using a forming gas;
- forming a second insulating layer including a transition element oxide on the first insulating layer;
- forming a third insulating layer by nitrifying the second insulating layer using a forming gas; and
- forming a conducting layer on top of the third insulating layer.

14. (Original) A method as defined in claim 13, wherein forming the second insulating layer comprises performing CVD.

15. (Original) A method as defined in claim 13, wherein the second insulating layer comprises an oxide of one of Ta, Al, Zr, V, Ti, Ni, and Hf.

16. (Cancelled)

17. (Cancelled)

18. (Cancelled)

19. (Cancelled)